



US 20240213033A1

(19) **United States**

(12) **Patent Application Publication**
Han et al.

(10) **Pub. No.: US 2024/0213033 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **SELECTIVE ETCHING METHODS AND
ETCHING ASSEMBLIES**

Publication Classification

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(51) **Int. Cl.**
H01L 21/311 (2006.01)
H01J 37/32 (2006.01)
H01L 21/027 (2006.01)
H01L 21/67 (2006.01)

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(52) **U.S. Cl.**
CPC .. *H01L 21/31144* (2013.01); *H01J 37/32899* (2013.01); *H01L 21/0271* (2013.01); *H01L 21/31116* (2013.01); *H01L 21/67069* (2013.01); *H01J 2237/3341* (2013.01)

(21) Appl. No.: **18/544,516**

(22) Filed: **Dec. 19, 2023**

Related U.S. Application Data

(60) Provisional application No. 63/434,202, filed on Dec. 21, 2022.

(57) **ABSTRACT**

The current disclosure relates to methods and assemblies for selectively etching a material from a first surface of a substrate relative to a second surface of the same substrate. The second surface of the substrate is covered by an organic polymer layer and the first surface is etched by a reactive species generated from NF_3 -containing plasma. The current disclosure further relates to semiconductor structures and devices formed by using the methods or assemblies of the disclosure.

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